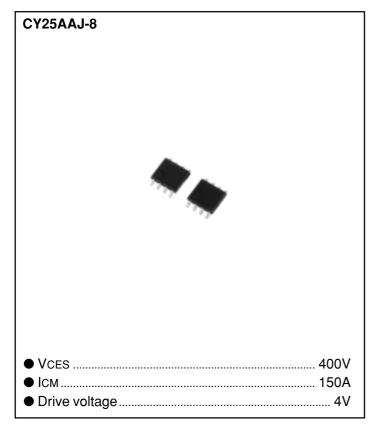
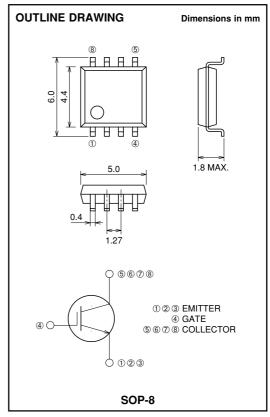
CY25AAJ-8

Nch IGBT for STROBE FLASHER





APPLICATION

Strobe flasher for Camera

MAXIMUM RATINGS (Tc = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
VCES	Collector-emitter voltage	VGE = 0V	400	V
VGES	Gate-emitter voltage	VCE = 0V	±6	V
VGEM	Peak gate-emitter voltage	VCE = 0V, tw = 10s	±8	V
Ісм	Collector current (Pulsed)	CM = 400μF see figure1	150	Α
Tj	Junction temperature		− 40 ~ +150	°C
Tstg	Storage temperature		− 40 ~ +150	°C



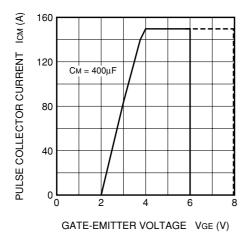
CY25AAJ-8

Nch IGBT for STROBE FLASHER

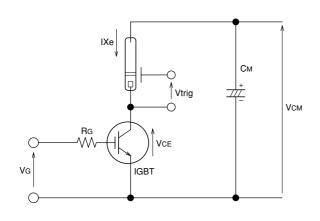
ELECTRICAL CHARACTERISTICS (Tj = 25°C)

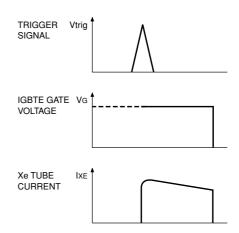
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Тур.	Max.	Offic
V (BR) CES	Collector-emitter breakdown voltage	IC = 1mA, VGE = 0V	450	_	_	V
ICES	Collector-emitter leakage current	VCE = 400V, VGE = 0V	_	_	10	μΑ
IGES	Gate-emitter leakage current	$VGE = \pm 6V$, $VCE = 0V$	_	_	±0.1	μΑ
VGE (th)	Gate-emitter threshold voltage	VCE = 10V, IC = 1mA	_	_	1.5	V

Figure 1. MAXIMUM PULSE COLLECTOR CURRENT



APPLICATION EXAMPLE





Recommended operation conditions Maximum operation conditions

VCM = 330VVCM = 350VICP = 130A ICP = 150A $CM = 330 \mu F$ $\text{CM} = 400 \mu \text{F}$ VGE = 5V

Notice 1. Gate drive voltage during on-state must be applied to satisfy the rating of maximum pulse collector current. And peak reverse gate current during turn-off must become less than 0.1A. (In general, when RG (off) = 30Ω , it is satisfied.)

Notice 2. IGBT has MOS structure and its gate is insulated by thin silicon oxide.

So please handle carefully not to give static electricity.

Notice 3. The operation life should be endured 5,000 shots under the charge current

(Ixe \leq 150A: full luminescence condition) of main condenser (CM = 400 μ F).

Repetitive period under the full luminescence conditions is over 3 seconds.

Notice 4. Total gate operation time must be applied within 5,000 hours.

